

## IGBT Chip in NPT-technology

### FEATURES:

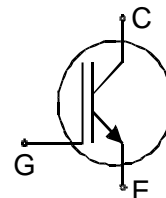
- 1200V NPT technology
- 200µm chip
- short circuit prove
- positive temperature coefficient
- easy paralleling

### This chip is used for:

- BUP 311D /BUP 212

### Applications:

- drives



Chip Type	V <sub>CE</sub>	I <sub>CN</sub>	Die Size	Package	Ordering Code
SIGC16T120C	1200V	8A	4.04 x 4 mm <sup>2</sup>	sawn on foil	Q67041-A4673-A003

### MECHANICAL PARAMETER:

Raster size	4.04 x 4	mm <sup>2</sup>
Area total / active	16.16 / 10.4	
Emitter pad size	1.88x2.18	
Gate pad size	0.71x1.08	
Thickness	200	µm
Wafer size	150	mm
Flat position	0	deg
Max.possible chips per wafer	898 pcs	
Passivation frontside	Photoimide	
Emitter metalization	3200 nm Al Si 1%	
Collector metalization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

## MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage, $T_j=25\text{ °C}$	$V_{CE}$	1200	V
DC collector current, limited by $T_{jmax}$	$I_C$	<sup>1)</sup>	A
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	24	A
Gate emitter voltage	$V_{GE}$	$\pm 20$	V
Operating junction and storage temperature	$T_j, T_{stg}$	-55 ... +150	°C

<sup>1)</sup> depending on thermal properties of assembly

## STATIC CHARACTERISTICS (tested on chip), $T_j=25\text{ °C}$ , unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=500\mu A$	1200			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=8A$	2	2.5	3	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=350\mu A, V_{GE}=V_{CE}$	4.5	5.5	6.5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$			1	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$			120	nA

## DYNAMIC CHARACTERISTICS (tested at component):

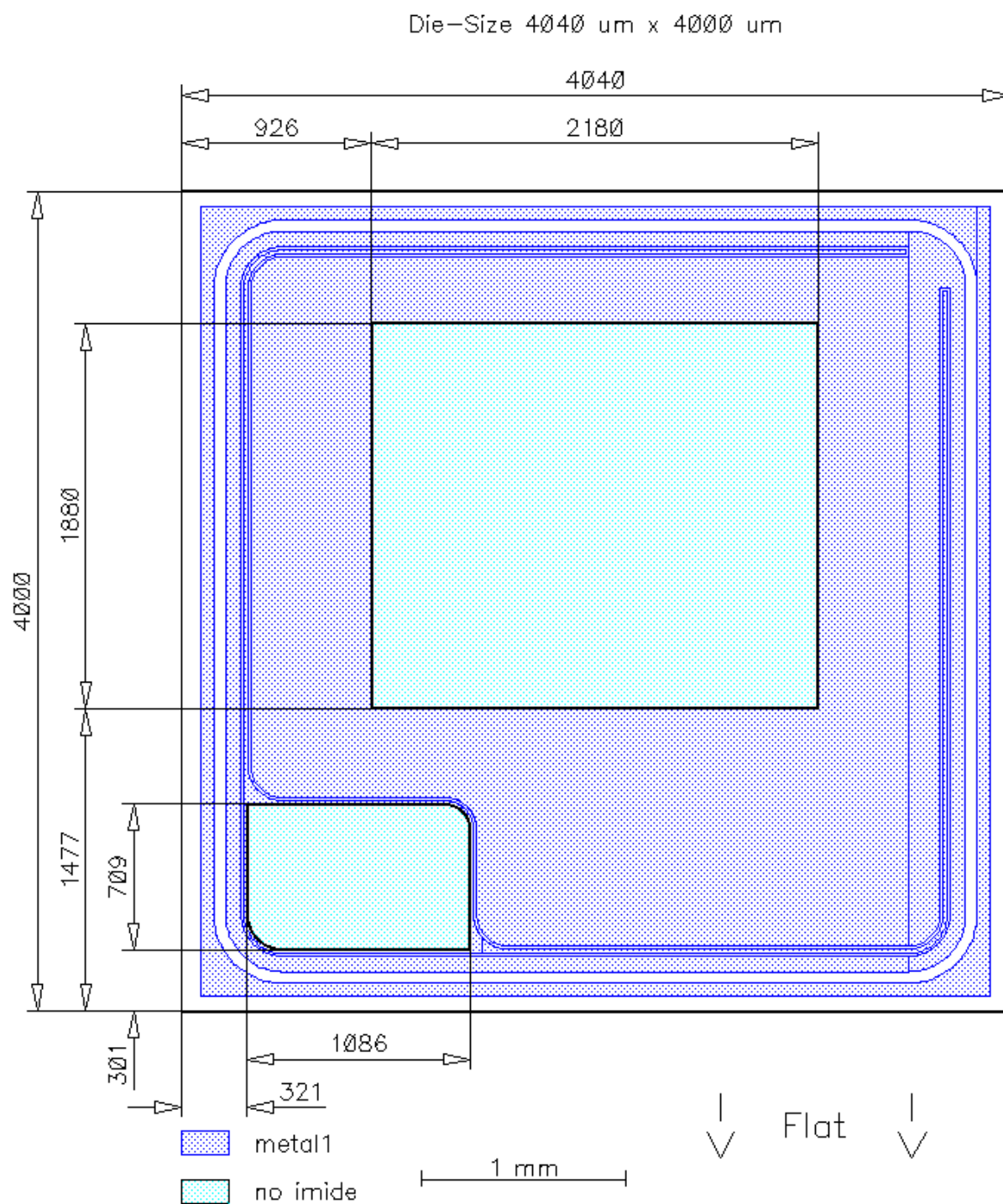
Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	$C_{iss}$	$V_{CE}=25V,$	-	600	800	pF
Output capacitance	$C_{oss}$	$V_{GE}=0V,$	-	60	90	
Reverse transfer capacitance	$C_{rss}$	$f=1MHz$	-	38	55	

## SWITCHING CHARACTERISTICS (tested at component), Inductive Load:

Parameter	Symbol	Conditions <sup>1)</sup>	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125\text{ °C}$ $V_{CC}=600V,$ $I_C=8A$ $V_{GE}=\pm 15V,$ $R_G=150\Omega$	-	55	110	ns
Rise time	$t_r$		-	50	100	
Turn-off delay time	$t_{d(off)}$		-	380	570	
Fall time	$t_f$		-	80	120	

<sup>1)</sup> values also influenced by parasitic L- and C- in measurement and package.

## CHIP DRAWING:



---

**FURTHER ELECTRICAL CHARACTERISTICS:**

---

This chip data sheet refers to the  
device data sheet

BUP 311D /BUP 212

Package : TO220

---

---

**Description:**

---

AQL 0,65 for visual inspection according to failure catalog

---

Electrostatic Discharge Sensitive Device according to MIL-STD 883

---

Test-Normen Villach/Prüffeld

---

**Published by**  
**Infineon Technologies AG,**  
**Bereich Kommunikation**  
**St.-Martin-Strasse 53,**  
**D-81541 München**  
**© Infineon Technologies AG 2002**  
**All Rights Reserved.**

**Attention please!**

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

**Information**

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives world-wide (see address list).

**Warnings**

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and / or maintain and sustain and / or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.